

6367254 MOTOROLA SC {XSTRS/R F}

96D 82012 D

T-3I-25

**MAXIMUM RATINGS**

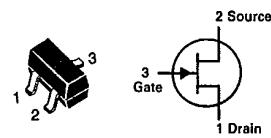
Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	25	Vdc
Gate-Source Voltage	$V_{GS}$	25	Vdc
Gate Current	$I_G$	10	mAdc

**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{mW}$
Total Device Dissipation Alumina Substrate,** $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300	mW
		2.4	mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{mW}$
Junction and Storage Temperature	$T_J, T_{stg}$	150	$^\circ\text{C}$

\*FR-5 =  $1.0 \times 0.75 \times 0.62$  in.\*\*Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.**DEVICE MARKING**

MMBFJ310 = 6T

**MMBFJ310****CASE 318-02/03, STYLE 10  
SOT-23 (TO-236AA/AB)****JFET  
VHF/UHF AMPLIFIER  
TRANSISTOR**

N-CHANNEL

**ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$  unless otherwise noted.)**

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Gate-Source Breakdown Voltage ( $I_G = -1.0 \mu\text{Adc}, V_{DS} = 0$ )	$V_{(BR)GSS}$	-25	—	—	Vdc
Gate Reverse Current ( $V_{GS} = -15$ V) ( $V_{GS} = -15$ V, $T_A = 125^\circ\text{C}$ )	$I_{GSS}$	—	—	-1.0 -1.0	nAdc $\mu\text{Adc}$
Gate Source Cutoff Voltage ( $V_{DS} = 10$ Vdc, $I_D = 1.0$ nAdc)	$V_{GS(\text{off})}$	-2.0	—	-6.5	Vdc
<b>ON CHARACTERISTICS</b>					
Zero-Gate-Voltage Drain ( $V_{DS} = 10$ Vdc, $V_{GS} = 0$ )	$I_{DSS}$	24	—	60	mAdc
Gate-Source Forward Voltage ( $I_G = 1.0$ mAdc, $V_{DS} = 0$ )	$V_{GS(f)}$	—	—	1.0	Vdc
<b>SMALL-SIGNAL CHARACTERISTICS</b>					
Forward Transfer Admittance ( $V_{DS} = 10$ Vdc, $I_D = 10$ mAdc, $f = 1.0$ kHz)	$ Y_{fs} $	8.0	—	18	mmhos
Output Admittance ( $V_{DS} = 10$ Vdc, $I_D = 10$ mAdc, $f = 1.0$ kHz)	$ Y_{os} $	—	—	200	$\mu\text{mhos}$
Input Capacitance ( $V_{GS} = -10$ Vdc, $V_{DS} = 0$ Vdc, $f = 1.0$ MHz)	$C_{iss}$	—	—	5.0	pF
Reverse Transfer Capacitance ( $V_{GS} = -10$ Vdc, $V_{DS} = 0$ Vdc, $f = 1.0$ MHz)	$C_{rss}$	—	—	2.5	pF
Equivalent Short-Circuit Input Noise Voltage ( $V_{DS} = 10$ Vdc, $I_D = 10$ mAdc, $f = 100$ Hz)	$\bar{e}_n$	—	10	—	nV/ $\sqrt{\text{Hz}}$

MOTOROLA SMALL-SIGNAL SEMICONDUCTORS